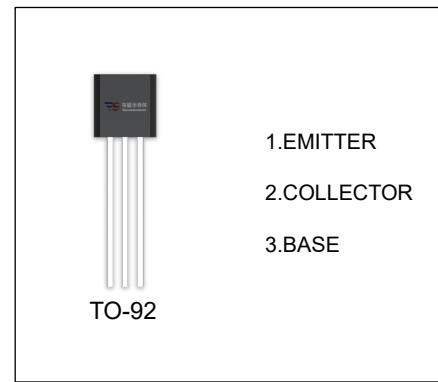


2N3828 TRANSISTOR (NPN)

FEATURES

- General Purpose Amplifier Transistor



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2N3828	TO-92	Bulk	1000pcs/Bag
2N3828-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	3	V
I_c	Collector Current -Continuous	0.1	A
P_D	Collector Power Dissipation	625	mW
R_{KJA}	Thermal Resistance from Junction to Ambient	200	$^\circ\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^\circ\text{C}$

$T_a=25^\circ C$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.01mA, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.01mA, I_C=0$	3			V
Collector cut-off current	I_{CBO}	$V_{CB}=60V, I_E=0$			0.1	7A
Collector cut-off current	I_{CEX}	$V_{CE}=30V, V_{BE^{off}}=3V$			50	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	7A
DC current gain	h_{FE}	$V_{CE}=1V, I_C=12mA$	30		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50mA, I_B=5mA$			0.3	V
Base-emitter saturation voltage	$V_{BE\ (sat)}$	$I_C=50mA, I_B=5mA$			0.95	V
Transition frequency	f_T	$V_{CE}=20V, I_C=10mA, f=100 MHz$	360			MHz